

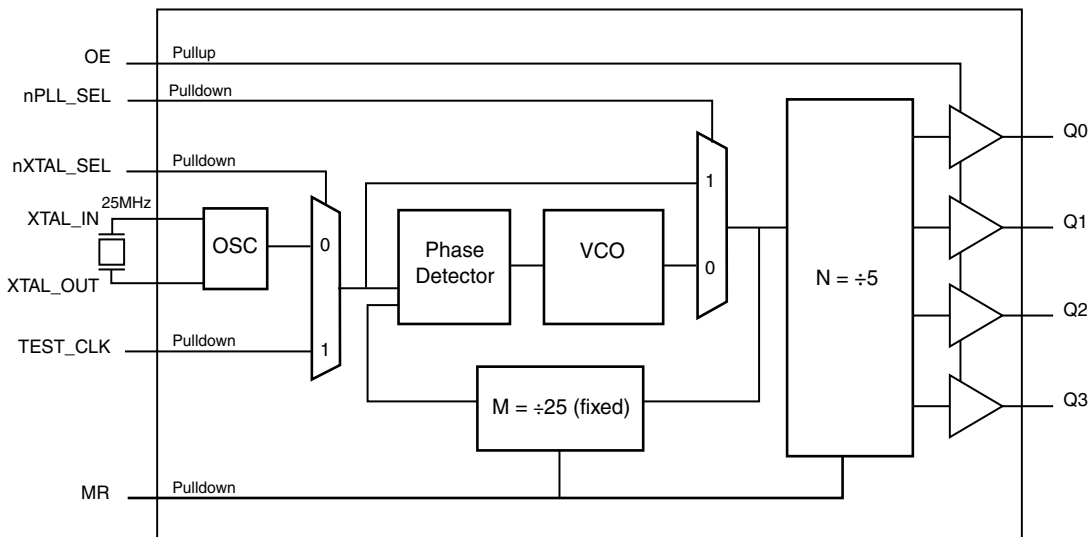
## General Description

The 840024I is a four output LVCMOS/LVTTL Synthesizer optimized to generate Ethernet reference clock frequency. The 840024I uses IDT's 3<sup>RD</sup> generation low phase noise VCO technology and can achieve 1ps or lower typical random RMS phase jitter, easily meeting Ethernet jitter requirements. The 840024I is packaged in a small 20-pin TSSOP package.

## Features

- Four LVCMOS / LVTTL outputs
- Selectable crystal oscillator interface or LVCMOS / LVTTL single-ended clock input
- Supports the following output frequency: 125MHz
- RMS phase jitter @125MHz (1.875MHz - 20MHz): 0.6ps (typical)
- Power supply modes:  
Core/Output  
3.3V/3.3V  
3.3V/2.5V  
2.5V/2.5V
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

## Block Diagram



## Pin Assignment

nc	1	20	nc
nc	2	19	GND
nXTAL_SEL	3	18	Q0
TEST_CLK	4	17	Q1
OE	5	16	VDDO
MR	6	15	Q2
nPLL_SEL	7	14	Q3
VDDA	8	13	GND
nc	9	12	XTAL_IN
VDD	10	11	XTAL_OUT

**20-Lead TSSOP**  
**6.5mm x 4.4mm x 0.925mm**  
**package body**  
**G Package**  
**Top View**

**Table 1. Pin Descriptions**

Number	Name	Type		Description
1, 2, 9, 20	nc	Unused		No connect pins.
3	nXTAL_SEL	Input	Pulldown	PLL reference select control input. See Table 3A. LVCMOS/LVTTL interface levels.
4	TEST_CLK	Input	Pulldown	Single-ended clock input. LVCMOS/LVTTL interface levels.
5	OE	Input	Pullup	Output enable control pin. See Table 3B. LVCMOS/LVTTL interface levels.
6	MR	Input	Pulldown	Master reset control pin. See Table 3C. LVCMOS/LVTTL interface levels.
7	nPLL_SEL	Input	Pulldown	PLL bypass control input. See Table 3D. LVCMOS/LVTTL interface levels.
8	V <sub>DDA</sub>	Power		Analog supply pin.
10	V <sub>DD</sub>	Power		Core supply pin.
11, 12	XTAL_OUT, XTAL_IN	Input		Crystal oscillator interface. XTAL_IN is the input. XTAL_OUT is the output.
13, 19	GND	Power		Power supply ground.
14, 15, 17, 18	Q3, Q2, Q1, Q0	Output		Single-ended clock outputs. 17Ω output impedance. LVCMOS/LVTTL interface levels.
16	V <sub>DDO</sub>	Power		Output supply pin.

NOTE: *Pullup* and *Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

**Table 2. Pin Characteristics**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C <sub>IN</sub>	Input Capacitance			4		pF
C <sub>PD</sub>	Power Dissipation Capacitance (per output)			8		pF
R <sub>PULLUP</sub>	Input Pullup Resistor			51		kΩ
R <sub>PULLDOWN</sub>	Input Pulldown Resistor			51		kΩ
R <sub>OUT</sub>	Output Impedance	V <sub>DDO</sub> = 3.3V ± 5%		17		Ω
		V <sub>DDO</sub> = 2.5V ± 5%		21		Ω

## Function Tables

**Table 3A. nXTAL\_SEL PLL Reference Select Function Table**

nXTAL_SEL	PLL Reference Input
0 (default)	XTAL Interface
1	TEST_CLK

**Table 3B. Output Enable Function Table**

OE	Output Operation
0	Q[0:3] are disabled in high-impedance state.
1 (default)	Q[0:3] are enabled.

**Table 3C. Master Reset Function Table**

MR	Reset Operation
0 (default)	Normal operation, internal dividers are enabled.
1	Internal dividers are reset, Q[0:3] are disabled in logic low state.

**Table 3D. PLL Bypass Function Table**

nPLL_SEL	PLL Operation
0 (default)	PLL is enabled
1	PLL is bypassed. The output frequency is equal to the selected reference frequency divided by the output divider of 5.

## Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, $V_{DD}$	4.6V
Inputs, $V_I$ XTAL_IN Other Inputs	0V to $V_{DD}$ -0.5V to $V_{DD} + 0.5V$
Outputs, $V_O$	-0.5V to $V_{DDO} + 0.5V$
Package Thermal Impedance, $\theta_{JA}$	86.7°C/W (0 mps)
Storage Temperature, $T_{STG}$	-65°C to 150°C

## DC Electrical Characteristics

**Table 4A. Power Supply DC Characteristics,  $V_{DD} = V_{DDO} = 3.3V \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{DD}$	Core Supply Voltage		3.135	3.3	3.465	V
$V_{DDA}$	Analog Supply Voltage		$V_{DD} - 0.14$	3.3	$V_{DD}$	V
$V_{DDO}$	Output Supply Voltage		3.135	3.3	3.465	V
$I_{DD}$	Core Supply Current				90	mA
$I_{DDA}$	Analog Supply Current				14	mA
$I_{DDO}$	Output Supply Current	No Load			8	mA

**Table 4B. Power Supply DC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $V_{DDO} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{DD}$	Core Supply Voltage		3.135	3.3	3.465	V
$V_{DDA}$	Analog Supply Voltage		$V_{DD} - 0.14$	3.3	$V_{DD}$	V
$V_{DDO}$	Output Supply Voltage		2.375	2.5	2.625	V
$I_{DD}$	Core Supply Current				90	mA
$I_{DDA}$	Analog Supply Current				14	mA
$I_{DDO}$	Output Supply Current	No Load			8	mA

**Table 4C. Power Supply DC Characteristics,  $V_{DD} = V_{DDO} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{DD}$	Core Supply Voltage		2.375	2.5	2.625	V
$V_{DDA}$	Analog Supply Voltage		$V_{DD} - 0.14$	2.5	$V_{DD}$	V
$V_{DDO}$	Output Supply Voltage		2.375	2.5	2.625	V
$I_{DD}$	Core Supply Current				90	mA
$I_{DDA}$	Analog Supply Current				14	mA
$I_{DDO}$	Output Supply Current	No Load			8	mA

**Table 4D. LVCMOS/LVTTL DC Characteristics,  $T_A = -40^{\circ}\text{C}$  to  $85^{\circ}\text{C}$** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{IH}$	Input High Voltage	$V_{DD} = 3.465\text{V}$	2		$V_{DD} + 0.3$	V
		$V_{DD} = 2.625\text{V}$	1.7		$V_{DD} + 0.3$	V
$V_{IL}$	Input Low Voltage	$V_{DD} = 3.465\text{V}$	-0.3		0.8	V
		$V_{DD} = 2.625\text{V}$	-0.3		0.7	V
$I_{IH}$	Input High Current	OE $V_{DD} = V_{IN} = 3.465\text{V}$ or $2.625\text{V}$			5	$\mu\text{A}$
		TEST_CLK, MR, nXTAL_SEL, nPLL_SEL $V_{DD} = V_{IN} = 3.465\text{V}$ or $2.625\text{V}$			150	$\mu\text{A}$
$I_{IL}$	Input Low Current	OE $V_{DD} = 3.465\text{V}$ or $2.625\text{V}$ , $V_{IN} = 0\text{V}$	-150			$\mu\text{A}$
		TEST_CLK, MR, nXTAL_SEL, nPLL_SEL $V_{DD} = 3.465\text{V}$ or $2.625\text{V}$ , $V_{IN} = 0\text{V}$	-5			$\mu\text{A}$
$V_{OH}$	Output High Voltage	$V_{DDO} = 3.3\text{V} \pm 5\%$ ; $I_{OH} = -12\text{mA}$	2.6			V
		$V_{DDO} = 2.5\text{V} \pm 5\%$ ; $I_{OH} = -12\text{mA}$	1.8			V
$V_{OL}$	Output Low Voltage	$V_{DDO} = 3.3\text{V} \pm 5\%$ or $2.5\text{V} \pm 5\%$ ; $I_{OL} = 12\text{mA}$			0.5	V

**Table 5. Crystal Characteristics**

Parameter	Test Conditions	Minimum	Typical	Maximum	Units
Mode of Oscillation		Fundamental			
Frequency			25		MHz
Equivalent Series Resistance (ESR)				50	$\Omega$
Shunt Capacitance				7	pF

NOTE: Characterized using an 18pF parallel resonant crystal.

## AC Electrical Characteristics

**Table 6A. AC Characteristics,  $V_{DD} = V_{DDO} = 3.3V \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$f_{OUT}$	Output Frequency			125		MHz
$t_{sk(o)}$	Output Skew; NOTE 1, 2			20	60	ps
$t_{jit}(\emptyset)$	RMS Phase Jitter (Random); NOTE 3	125MHz, Integration Range: 1.875MHz – 20MHz		0.604		ps
$t_{LOCK}$	PLL Lock Time			50	100	ms
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	250	400	750	ps
odc	Output Duty Cycle		42	50	58	%

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE: Characterized with crystal input.

NOTE 1: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at  $V_{DDO}/2$ .

NOTE 2: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 3: Refer to phase noise plots.

**Table 6B. AC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $V_{DDO} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$f_{OUT}$	Output Frequency			125		MHz
$t_{sk(o)}$	Output Skew; NOTE 1, 2			20	60	ps
$t_{jit}(\emptyset)$	RMS Phase Jitter (Random); NOTE 3	125MHz, Integration Range: 1.875MHz – 20MHz		0.546		ps
$t_{LOCK}$	PLL Lock Time			50	100	ms
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	250	400	750	ps
odc	Output Duty Cycle		46	50	54	%

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE: Characterized with crystal input.

NOTE 1: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at  $V_{DDO}/2$ .

NOTE 2: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 3: Refer to phase noise plots.

**Table 6C. AC Characteristics,  $V_{DD} = V_{DDO} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$f_{OUT}$	Output Frequency			125		MHz
$t_{sk(o)}$	Output Skew; NOTE 1, 2			20	60	ps
$t_{jit}(\emptyset)$	RMS Phase Jitter (Random); NOTE 3	125MHz, Integration Range: 1.875MHz – 20MHz		0.544		ps
$t_{LOCK}$	PLL Lock Time			50	100	ms
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	250	400	750	ps
odc	Output Duty Cycle		42	50	58	%

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

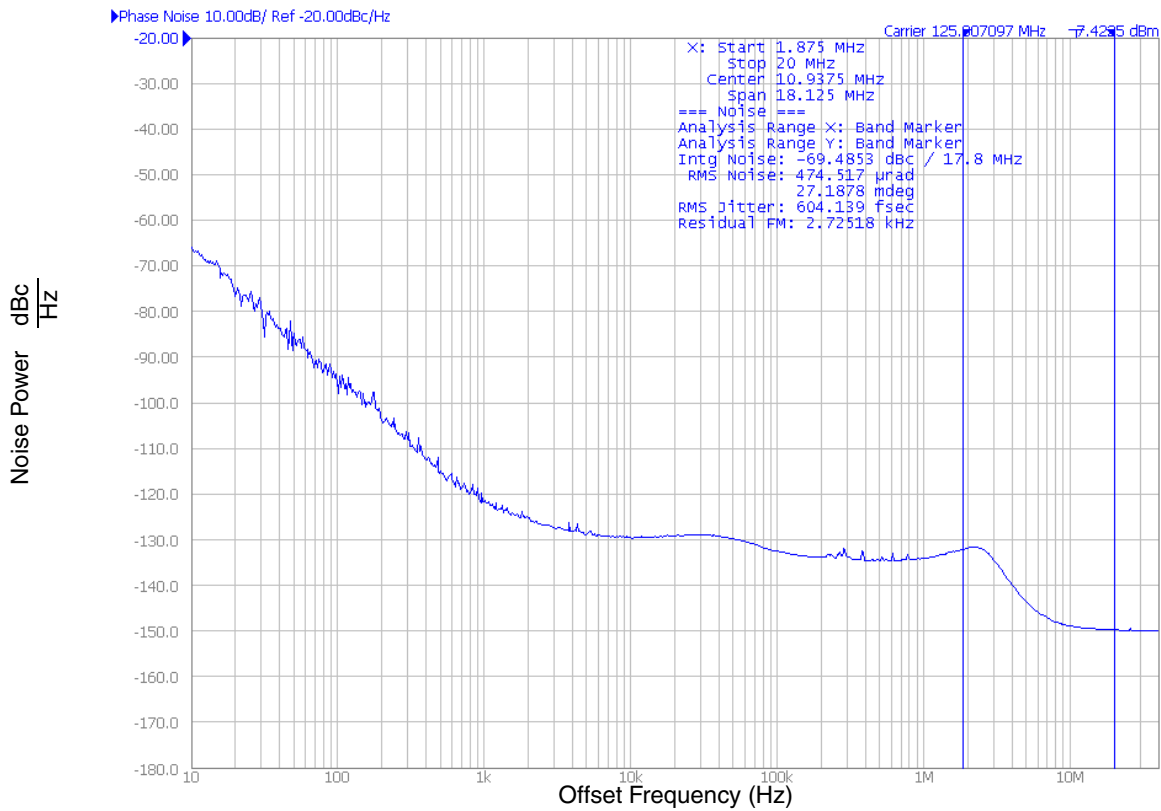
NOTE: Characterized with crystal input.

NOTE 1: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at  $V_{DDO}/2$ .

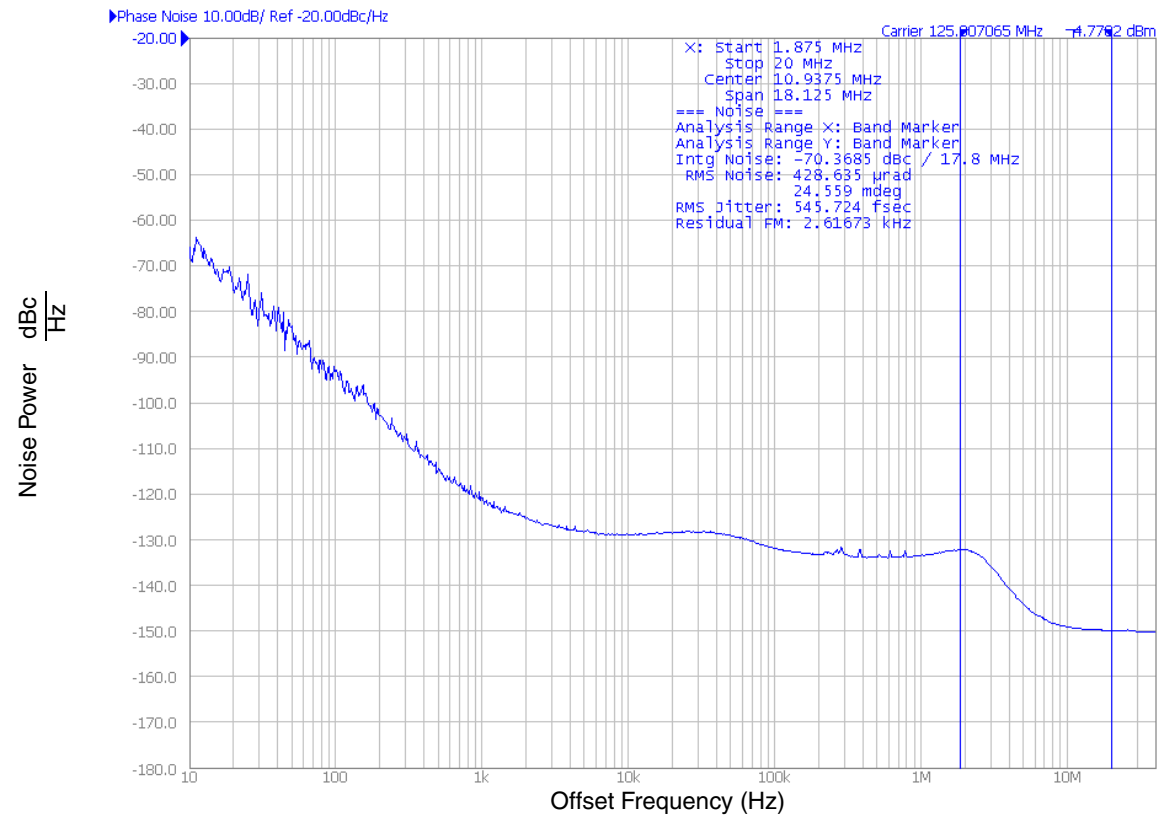
NOTE 2: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 3: Refer to phase noise plots.

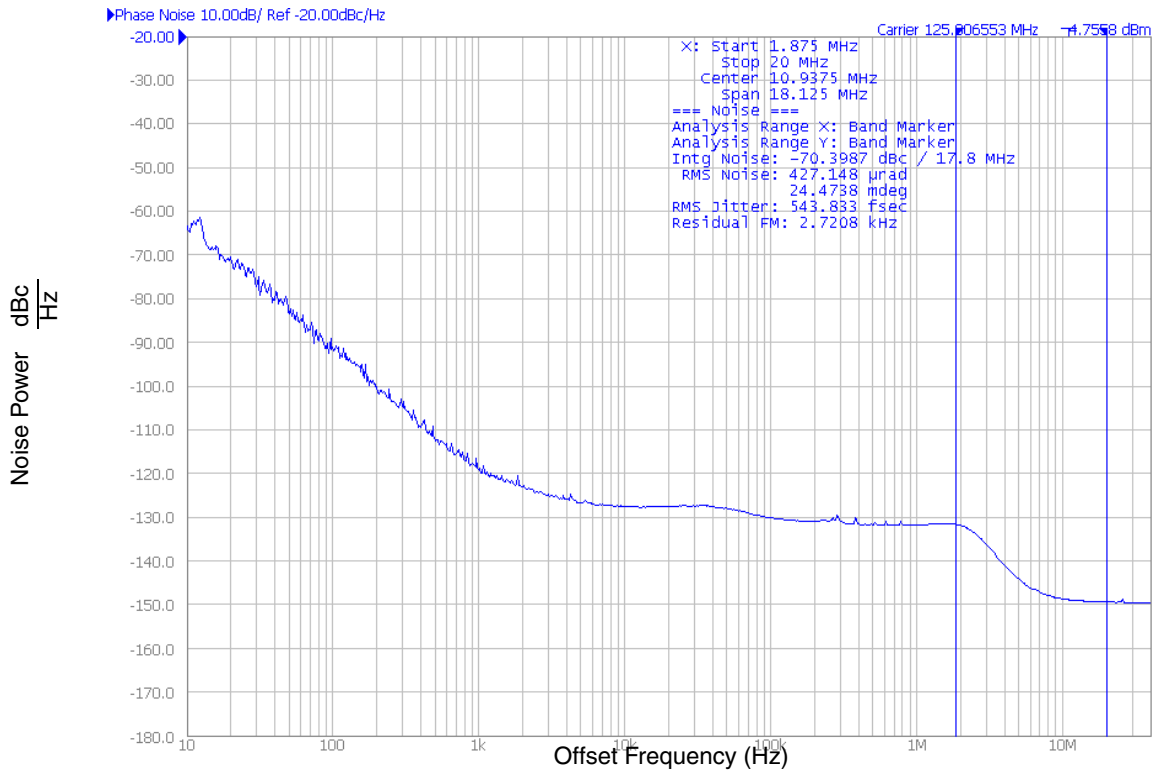
## Typical Phase Noise at 125MHz (3.3V/3.3V)



## Typical Phase Noise at 125MHz (3.3V/2.5V)

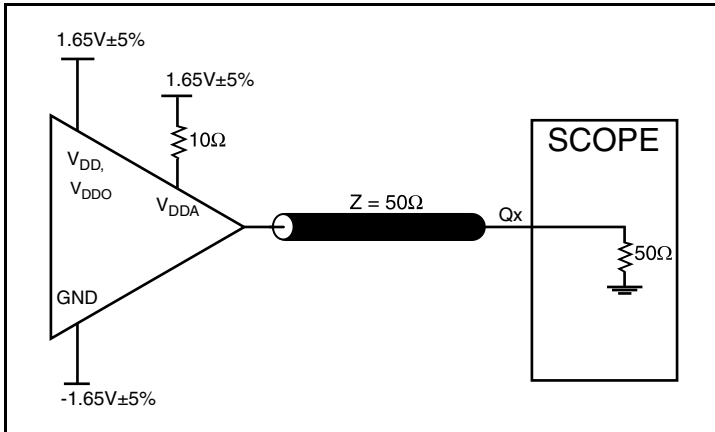


## Typical Phase Noise at 125MHz (2.5V/2.5V)

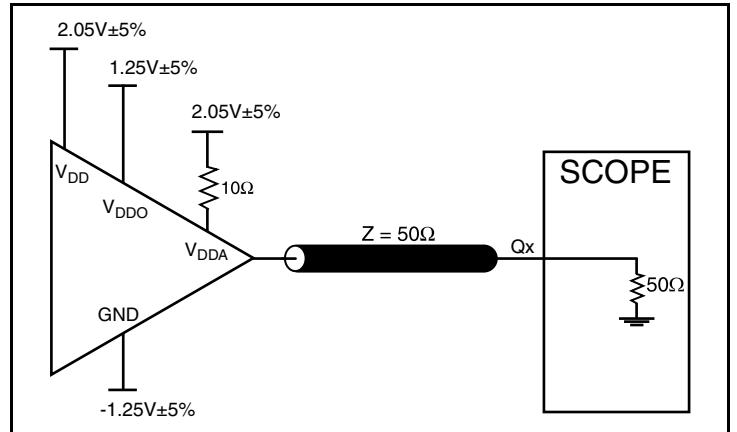




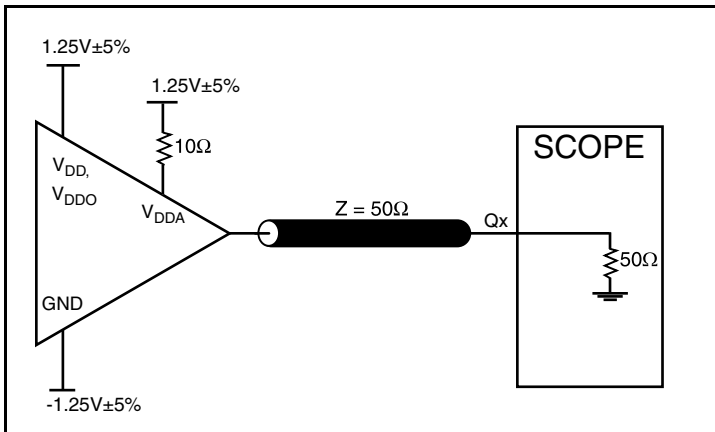
## Parameter Measurement Information



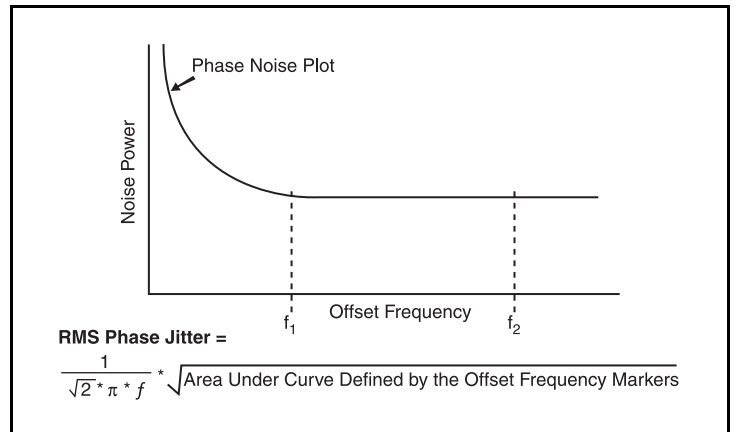
3.3V Core/3.3V LVCMOS Output Load AC Test Circuit



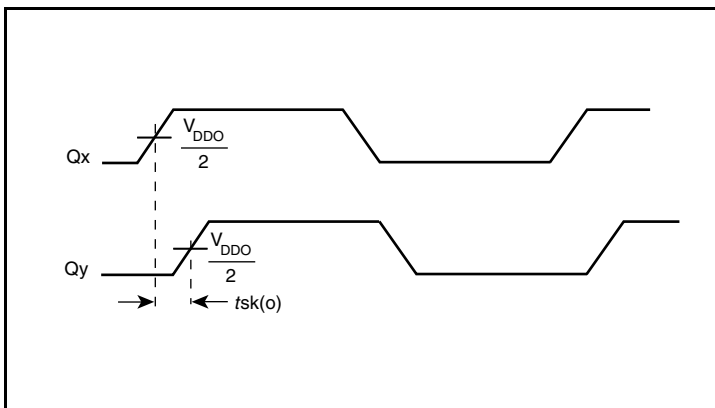
3.3V Core/2.5V LVCMOS Output Load AC Test Circuit



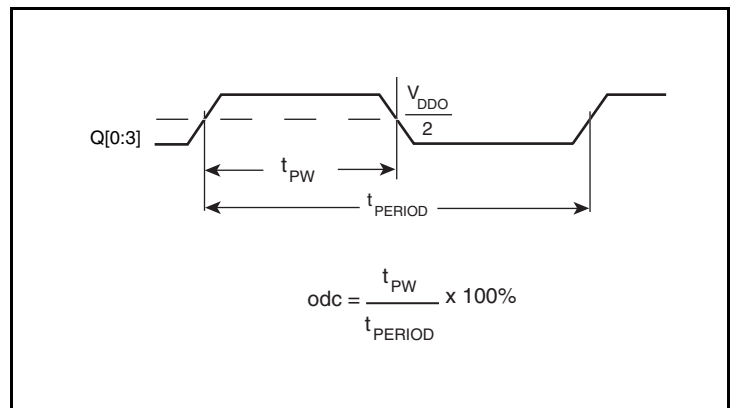
2.5V Core/2.5V LVCMOS Output Load AC Test Circuit



RMS Phase Jitter

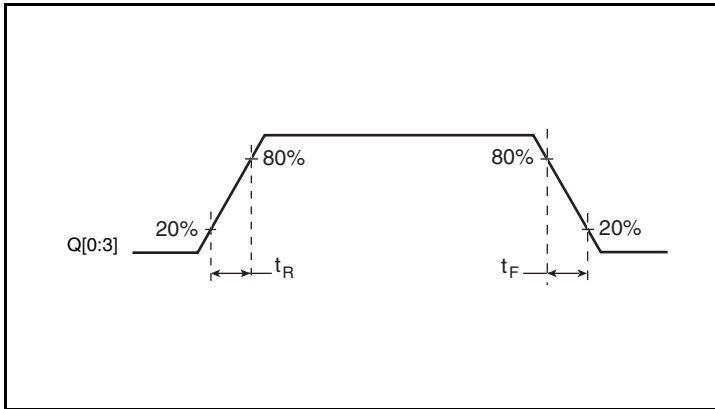


Output Skew



Output Duty Cycle/Pulse Width/Period

## Parameter Measurement Information, continued



**Output Rise/Fall Time**

## Applications Information

### Recommendations for Unused Input and Output Pins

#### Inputs:

##### TEST\_CLK Input

For applications not requiring the use of the test clock, it can be left floating. Though not required, but for additional protection, a 1k $\Omega$  resistor can be tied from the TEST\_CLK to ground.

##### LVC MOS Control Pins

All control pins have internal pullups or pulldowns; additional resistance is not required but can be added for additional protection. A 1k $\Omega$  resistor can be used.

#### Outputs:

##### LVC MOS Outputs

All unused LVC MOS outputs can be left floating. There should be no trace attached.

## Overdriving the XTAL Interface

The XTAL\_IN input can be overdriven by an LVCMOS driver or by one side of a differential driver through an AC coupling capacitor. The XTAL\_OUT pin can be left floating. The amplitude of the input signal should be between 500mV and 1.8V and the slew rate should not be less than 0.2V/nS. For 3.3V LVCMOS inputs, the amplitude must be reduced from full swing to at least half the swing in order to prevent signal interference with the power rail and to reduce internal noise. *Figure 1A* shows an example of the interface diagram for a high speed 3.3V LVCMOS driver. This configuration requires that the sum of the output impedance of the driver ( $R_o$ ) and the series resistance ( $R_s$ ) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This

can be done in one of two ways. First,  $R_1$  and  $R_2$  in parallel should equal the transmission line impedance. For most 50Ω applications,  $R_1$  and  $R_2$  can be 100Ω. This can also be accomplished by removing  $R_1$  and changing  $R_2$  to 50Ω. The values of the resistors can be increased to reduce the loading for a slower and weaker LVCMOS driver. *Figure 1B* shows an example of the interface diagram for an LVPECL driver. This is a standard LVPECL termination with one side of the driver feeding the XTAL\_IN input. It is recommended that all components in the schematics be placed in the layout. Though some components might not be used, they can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a quartz crystal as the input.

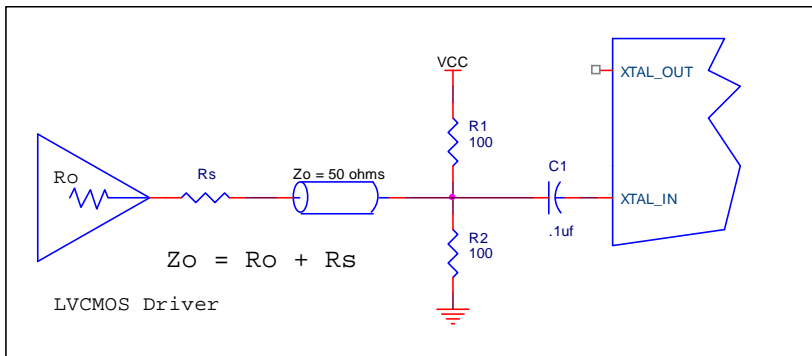


Figure 1A. General Diagram for LVCMOS Driver to XTAL Input Interface

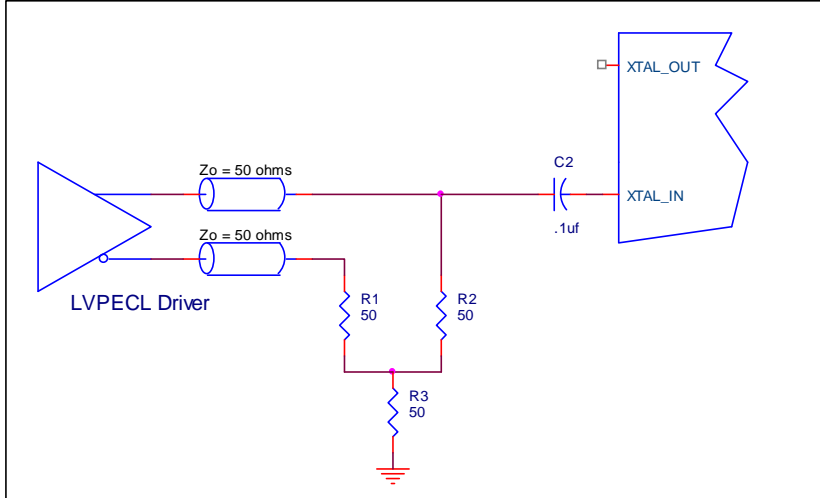


Figure 1B. General Diagram for LVPECL Driver to XTAL Input Interface

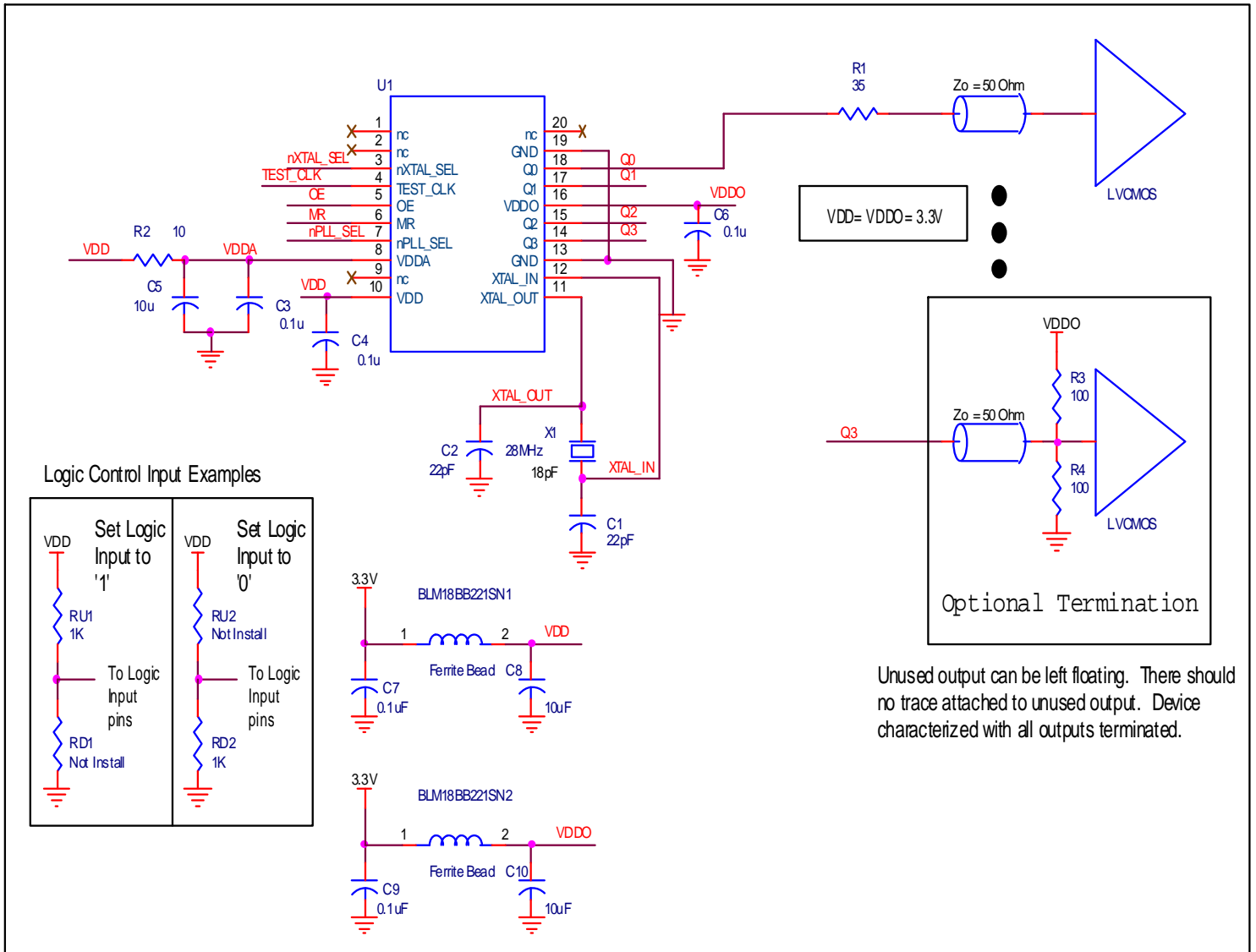
## Schematic Layout

Figure 2 shows an example of 840024I application schematic. In this example, the device is operated at  $V_{DD} = V_{DDO} = 3.3V$ . An 18pF parallel resonant 25MHz crystal is used. The load capacitance  $C1 = 22pF$  and  $C2 = 22pF$  are recommended for frequency accuracy. Depending on the parasitics of the printed circuit board layout, these values might require a slight adjustment to optimize the frequency accuracy. Crystals with other load capacitance specifications can be used. This will required adjusting  $C1$  and  $C2$ .

As with any high speed analog circuitry, the power supply pins are vulnerable to noise. To achieve optimum jitter performance, power

supply isolation is required. The 840024I provides separate power supplies to isolate from coupling into the internal PLL.

In order to achieve the best possible filtering, it is recommended that the placement of the filter components be on the device side of the PCB as close to the power pins as possible. If space is limited, the 0.1uF capacitor in each power pin filter should be placed on the device side of the PCB and the other components can be placed on the opposite side.



**Figure 2. 840024I Application Schematic**

Power supply filter recommendations are a general guideline to be used for reducing external noise from coupling into the devices. The filter performance is designed for wide range of noise frequencies. This low-pass filter starts to attenuate noise at approximately 10kHz. If a specific frequency noise component is known, such as switching power supply frequencies, it is recommended that component values be adjusted and if required, additional filtering be added. Additionally,

good general design practices for power plane voltage stability suggests adding bulk capacitances in the local area of all devices.

The schematic example focuses on functional connections and is not configuration specific. Refer to the pin description and functional tables in the datasheet to ensure the logic control inputs are properly set.

## Power Considerations

This section provides information on power dissipation and junction temperature for the 840024I. Equations and example calculations are also provided.

### 1. Power Dissipation.

The total power dissipation for the 840024I is the sum of the core power plus the analog power plus the output power dissipated into the load. The following is the power dissipation for  $V_{DD} = 3.3V + 5\% = 3.465V$ , which gives worst case results.

- Power (core)<sub>MAX</sub> =  $V_{DD\_MAX} * (I_{DD} + I_{DDA} + I_{DDO}) = 3.465V * (90mA + 14mA + 8mA) = \mathbf{388.1mW}$

### Dynamic Power Dissipation at 125MHz

$$\text{Power (125MHz)} = C_{PD} * \text{Frequency} * (V_{DD})^2 = 8pF * 125MHz * (3.465V)^2 = \mathbf{12mW \text{ per output}}$$

$$\text{Total Power (125MHz)} = 12mW * 4 = \mathbf{48mW}$$

### Total Power Dissipation

- Total Power**  
= Power (core)<sub>MAX</sub> + Power (125MHz)  
= 388.1mW + 48mW  
= **436.1mW**

### 2. Junction Temperature.

Junction temperature,  $T_j$ , is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature,  $T_j$ , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for  $T_j$  is as follows:  $T_j = \theta_{JA} * Pd\_total + T_A$

$T_j$  = Junction Temperature

$\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

$Pd\_total$  = Total Device Power Dissipation (example calculation is in section 1 above)

$T_A$  = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming no air flow and a multi-layer board, the appropriate value is 86.7°C/W per Table 7 below.

Therefore,  $T_j$  for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ\text{C} + 0.436W * 86.7^\circ\text{C/W} = 122.8^\circ\text{C}. \text{ This is below the limit of } 125^\circ\text{C}.$$

This calculation is only an example.  $T_j$  will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

**Table 7. Thermal Resistance  $\theta_{JA}$  for 20 Lead TSSOP, Forced Convection**

$\theta_{JA}$ vs. Air Flow			
Meters per Second	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	86.7°C/W	82.4°C/W	80.2°C/W

## Reliability Information

Table 8.  $\theta_{JA}$  vs. Air Flow Table for a 20 Lead TSSOP

$\theta_{JA}$ vs. Air Flow			
Meters per Second	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	86.7°C/W	82.4°C/W	80.2°C/W

## Transistor Count

The transistor count for ICS40024I is: 3093

## Package Outline and Package Dimensions

Package Outline - G Suffix for 20 Lead TSSOP

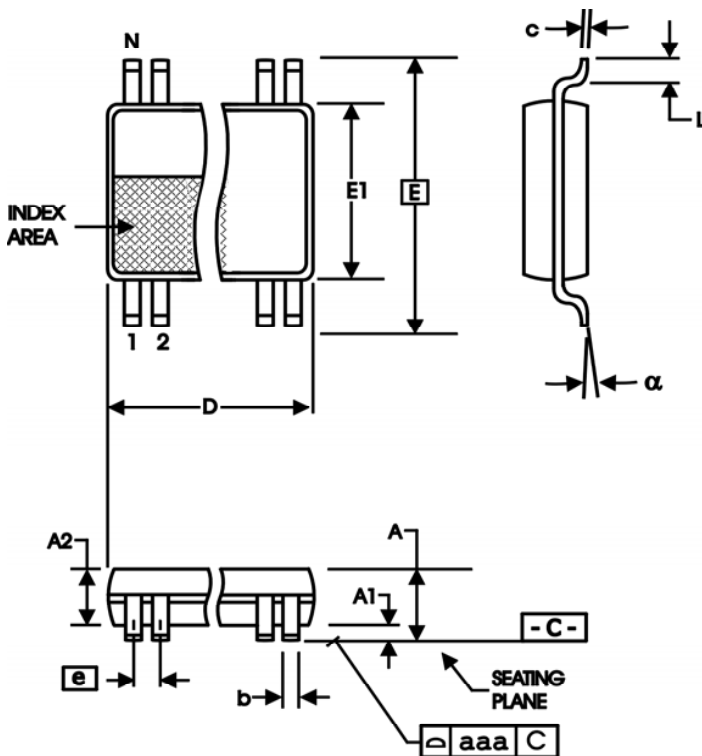


Table 9. Package Dimensions

All Dimensions in Millimeters		
Symbol	Minimum	Maximum
N	20	
A		1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	6.40	6.60
E	6.40 Basic	
E1	4.30	4.50
e	0.65 Basic	
L	0.45	0.75
$\alpha$	0°	8°
aaa		0.10

Reference Document: JEDEC Publication 95, MO-153

## Ordering Information

Table 10. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
840024BGILF	ICS840024BIL	"Lead-Free" 20 Lead TSSOP	Tube	-40°C to 85°C
840024BGILFT	ICS840024BIL	"Lead-Free" 20 Lead TSSOP	Tape & Reel	-40°C to 85°C

## Revision History Sheet

Rev	Table	Page	Description of Change	Date
B		1	Block Diagram - corrected nXTAL_SEL to select XTAL when LOW (0) and select TEST_CLK when HIGH (1).	8/30/2012
C	4A - 4C 6A - 6C	4 6	Output Supply Current, Test Conditions: Added 'No Load'. Added NOTE: Use XTAL input.	12/6/12
C	Features 4A - 4C 6A - 6C	1 4 6 13	Deleted 17 $\Omega$ Output Impedance. RMS Phase Jitter from 0.604ps to 0.6ps I <sub>DDA</sub> from 12mA to 14mA Deleted NOTE: Use XTAL input. Added NOTE: Characterized with crystal input. Updated Power Considerations for 14mA	1/11/13
C			Updated data sheet format.	4/3/15





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